

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		second near3 high near3 frequenc\$4 near3 lin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:25
		L3 and (high near3 frequency near3 transmission near4 line\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:22
		"masataka.in.	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:03
L1	12976	(high near3 frequency) same dielectric\$4	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:21
L2	35	L1 and 385/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:21
L3	2593	385/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:21
L4	10	L3 and (high near3 frequency near3 transmission near4 line\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:22
L5	946	dielectric and leadframe	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:22
L6	34	L5 and "385"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:22
L7	135	L5 and (high adj frequency)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:24

L8	120	(coplanar with waveguide\$4) and semiconductor and (high near3 frequenc\$4 near3 line\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 14:36
L9	4	mircostrip adj line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 15:00
L10	8879	(dielectric and high and frequency and transmission and line and carrier)".clm"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 15:01
L11	35	(dielectric and high and frequency and transmission and line and carrier).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 15:02
L12	11	(dielectric and high and frequency and transmission and line and carrier and electric).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 15:03
S1	976	matsushima.in.	US-PGPUB; USPAT	OR	OFF	2005/03/02 14:47
S2	11	S1 and transmission.ti.	US-PGPUB; USPAT	OR	OFF	2005/02/28 11:08
S3	11827	(high near3 frequency) same dielectric\$4	US-PGPUB; USPAT	OR	OFF	2005/02/28 11:22
S4	27	S3 and 385/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:21
S5	2288	385/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/02/28 13:16
S6	10	S5 and (high near3 frequency near3 transmission near4 line\$4)	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:21
S7	1	("4703996").PN. OR ("6856709").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 12:56
S8	0	("6856709").URPN.	USPAT	OR	OFF	2005/02/28 12:56
S9	1	("4703996").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 12:56

S10	102	lin.xa. and (high adj frequency)	US-PGPUB; USPAT	OR	OFF	2005/02/28 13:16
S11	3	lin.xa. and (high adj frequency) and tina.xa.	US-PGPUB; USPAT	OR	OFF	2005/02/28 13:22
S12	0	dielectric and 385/14/ccls.	US-PGPUB; USPAT	OR	OFF	2005/02/28 14:26
S13	848	dielectric and 385/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/02/28 14:29
S14	827	dielectric and leadframe	US-PGPUB; USPAT	OR	OFF	2005/02/28 14:29
S15	28	S14 and "385"/\$.ccls.	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:22
S16	123	S14 and (high adj frequency)	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:22
S17	6636	second near3 high near3 frequenc\$4	US-PGPUB; USPAT	OR	OFF	2005/02/28 14:32
S18	175	second near3 high near3 frequenc\$4 near3 lin\$4	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:25
S19	5155	waveguide\$4 and (high near3 frequenc\$4) and semiconductor	US-PGPUB; USPAT	OR	OFF	2005/03/01 20:00
S20	361	waveguide\$4 same (high near3 frequenc\$4) same semiconductor	US-PGPUB; USPAT	OR	OFF	2005/03/01 20:05
S21	28	waveguide\$4 same (high near3 frequenc\$4 near3 line\$4) same semiconductor.	US-PGPUB; USPAT	OR	OFF	2005/03/01 20:05
S22	98	(coplanar with waveguide\$4) and semiconductor and (high near3 frequenc\$4 near3 line\$4)	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:25
S23	166	(coplanar with waveguide\$4) and (high near3 frequenc\$4 near3 line\$4)	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:03
S24	0	"masataka.in."	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:03
S25	2967	masataka.in.	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:03
S26	37	masataka.in. and minoru.in.	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:27
S27	698	AlN with semiconductor with material\$4	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:31
S28	206	AlN with semiconductor with material\$4 with substrate	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:58
S29	3	microstrip adj line	US-PGPUB; USPAT	OR	OFF	2005/10/24 14:36
S30	346	(microstrip adj line) with coplanar	US-PGPUB; USPAT	OR	OFF	2005/03/02 15:59